

# VBA3316 Datasheet

## Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
30	0.016 at $V_{GS} = 10$ V	8.5	7.1
	0.020 at $V_{GS} = 4.5$ V	7.6	

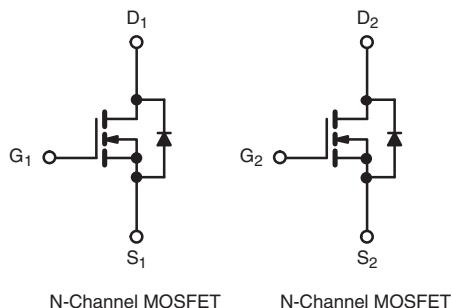
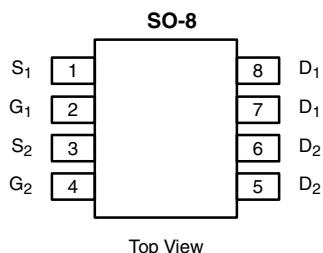
### FEATURES

- Trench Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT

### APPLICATIONS

- Notebook System Power
- Low Current DC/DC



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	8.5 7.5 7.2 <sup>b, c</sup> 5.9 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	30	A
Source-Drain Current Diode Current	$I_S$	2.8 1.8 <sup>b, c</sup>	
Pulsed Source-Drain Current	$I_{SM}$	30	
Single Pulse Avalanche Current	$I_{AS}$	10	
Single Pulse Avalanche Energy	$E_{AS}$	5	
Maximum Power Dissipation	$P_D$	3.1 2.0 2.0 <sup>b, c</sup> 1.25 <sup>b, c</sup>	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	52	62.5	°C/W
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	30	40	

Notes:

a. Based on  $T_C = 25$  °C.

b. Surface mounted on 1" x 1" FR4 board.

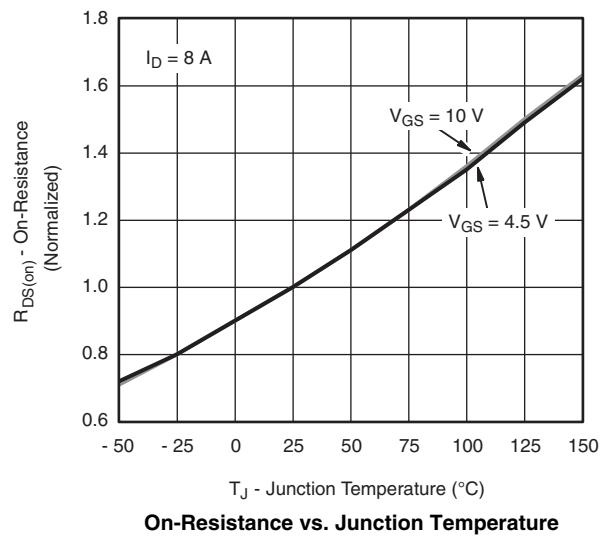
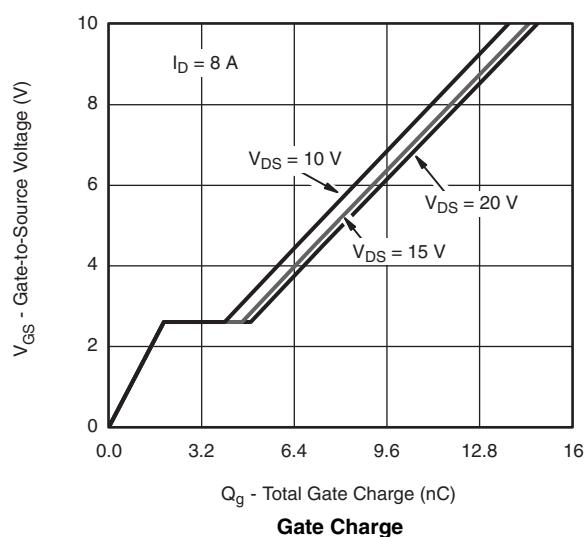
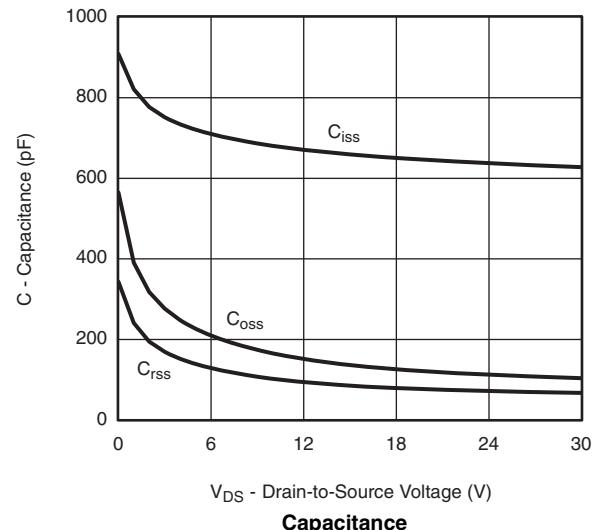
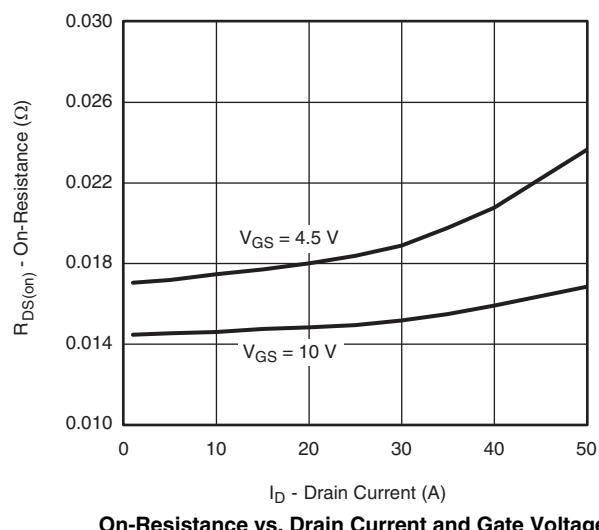
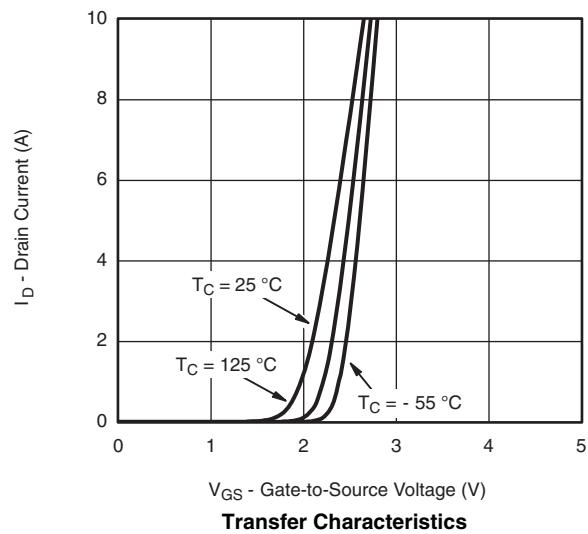
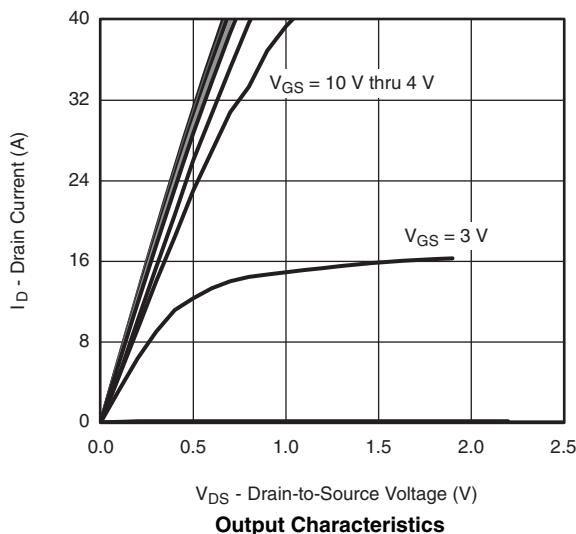
c.  $t = 10$  s.

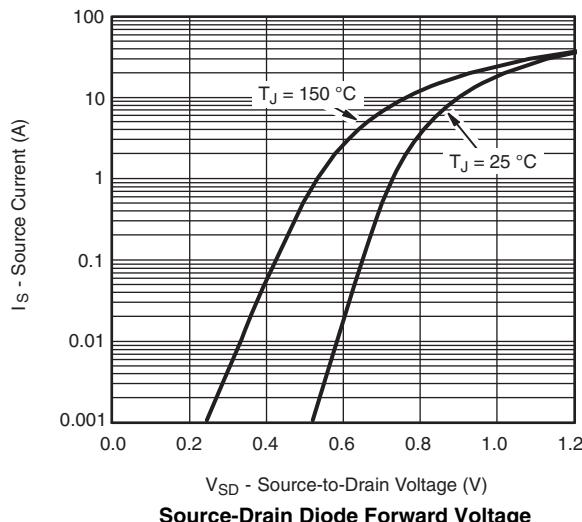
d. Maximum under steady state conditions is 110 °C/W.

**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

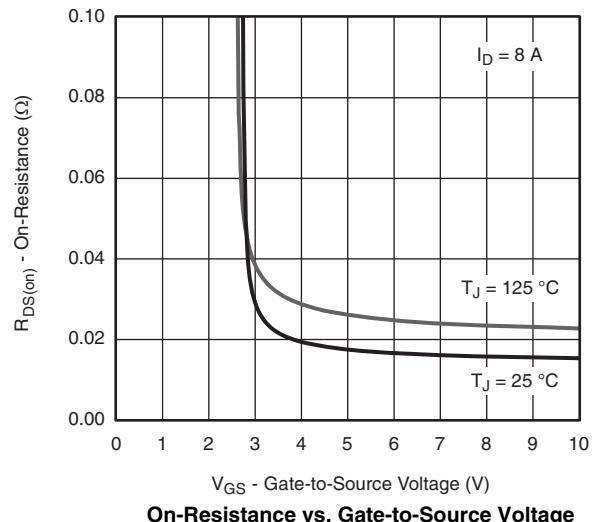
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		3.0		$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$	$I_D = 250 \mu\text{A}$		- 5.2		
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.2		2.5	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			10	
On -State Drain Current <sup>b</sup>	$I_{D(\text{on})}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$		0.016		$\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$		0.020		
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_D = 8 \text{ A}$		27		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1 \text{ MHz}$		660		$\text{pF}$
Output Capacitance	$C_{oss}$			140		
Reverse Transfer Capacitance	$C_{rss}$			86		
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$		14.5	22	$\text{nC}$
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$		7.1	11	
Gate-Drain Charge	$Q_{gd}$			1.9		
Gate Resistance	$R_g$		$f = 1 \text{ MHz}$	0.5	2.6	$\Omega$
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}, R_L = 3 \Omega$ $I_D \geq 5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		14	28	$\text{ns}$
Rise Time	$t_r$			45	80	
Turn-Off Delay Time	$t_{d(\text{off})}$			18	35	
Fall Time	$t_f$			12	24	
Turn-On Delay Time	$t_{d(\text{on})}$			7	14	
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(\text{off})}$			15	30	
Fall Time	$t_f$			7	14	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			2.8	$\text{A}$
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				30	
Body Diode Voltage	$V_{SD}$	$I_S = 2 \text{ A}$		0.77	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		17	34	$\text{ns}$
Body Diode Reverse Recovery Charge	$Q_{rr}$			9	18	$\text{nC}$
Reverse Recovery Fall Time	$t_a$			10		$\text{nS}$
Reverse Recovery Rise Time	$t_b$			7		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

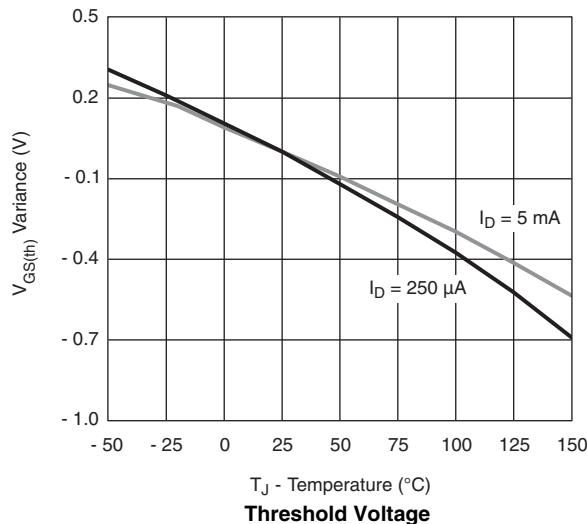
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


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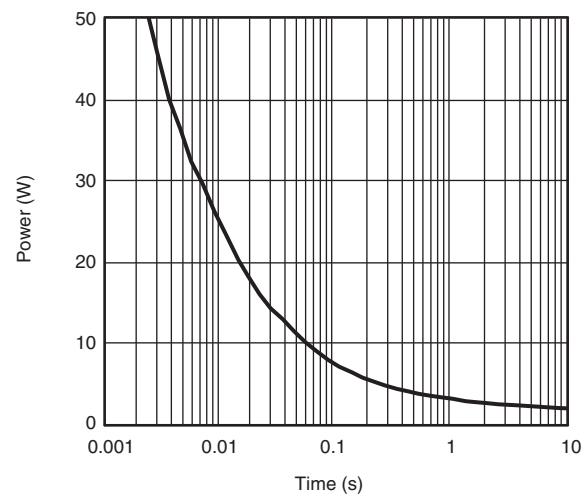
Source-Drain Diode Forward Voltage



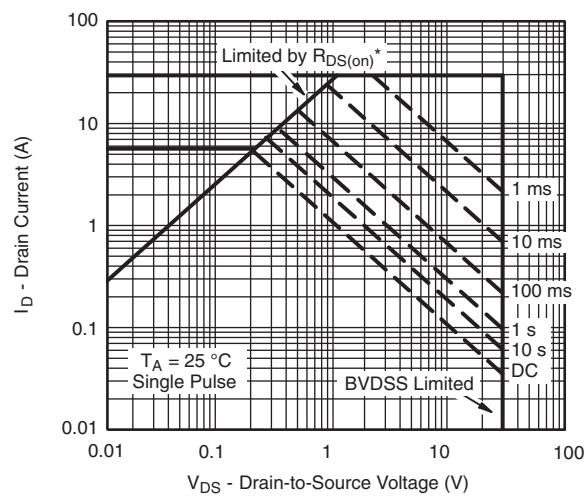
On-Resistance vs. Gate-to-Source Voltage



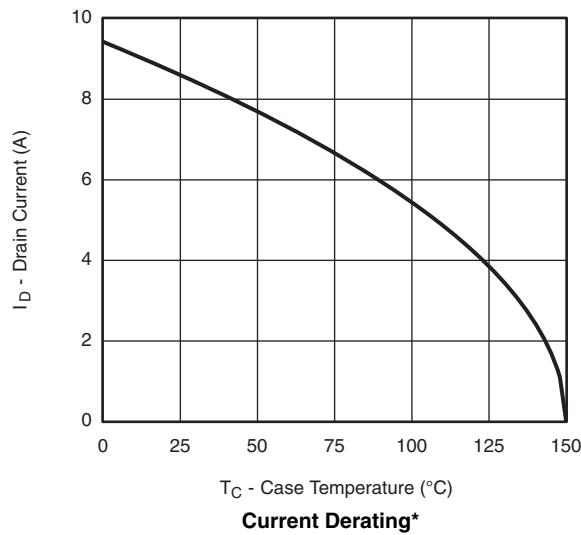
Threshold Voltage



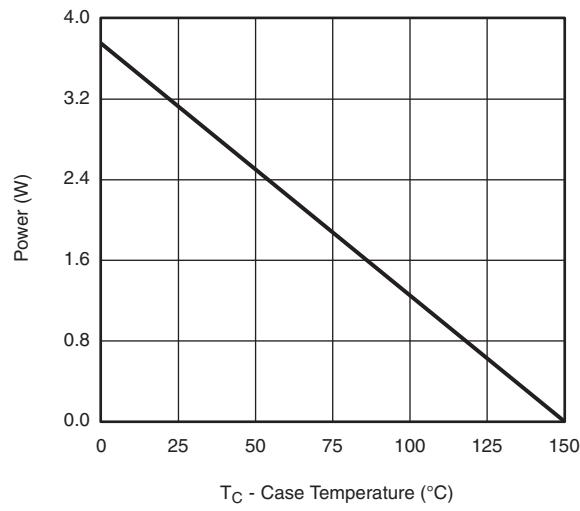
Single Pulse Power, Junction-to-Ambient

\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

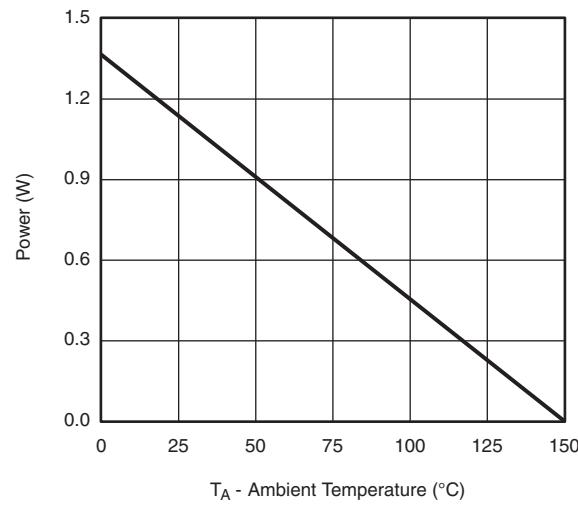
Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


Current Derating\*

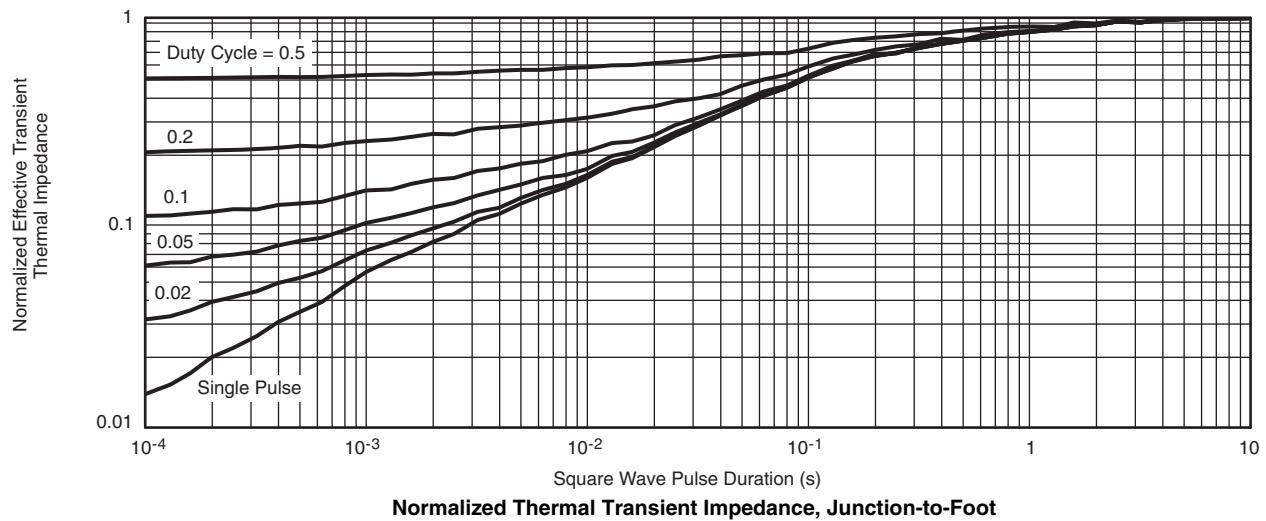
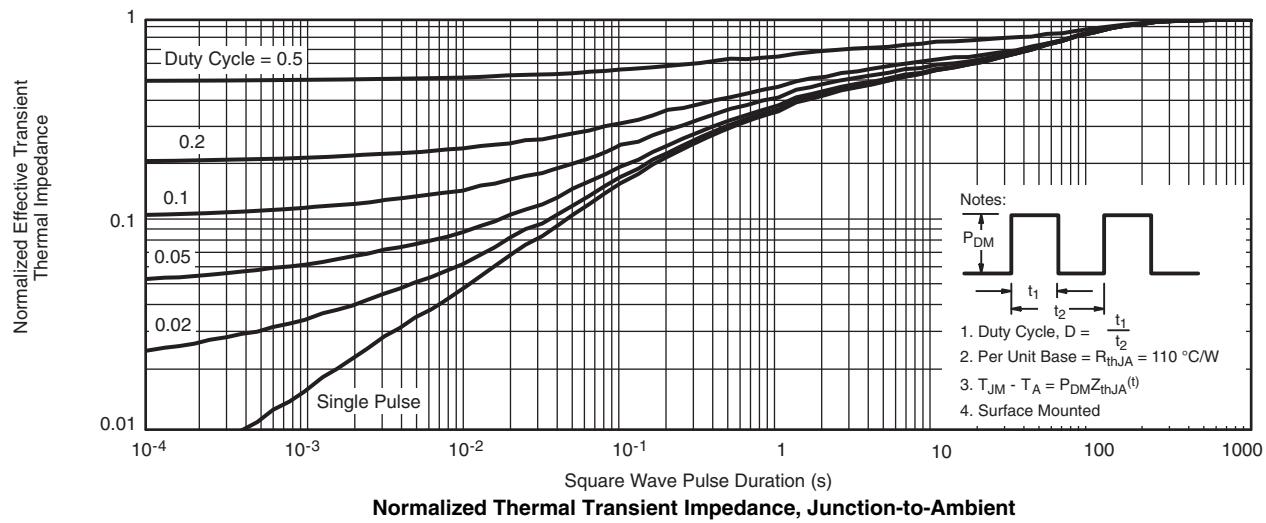


Power Derating, Junction-to-Foot



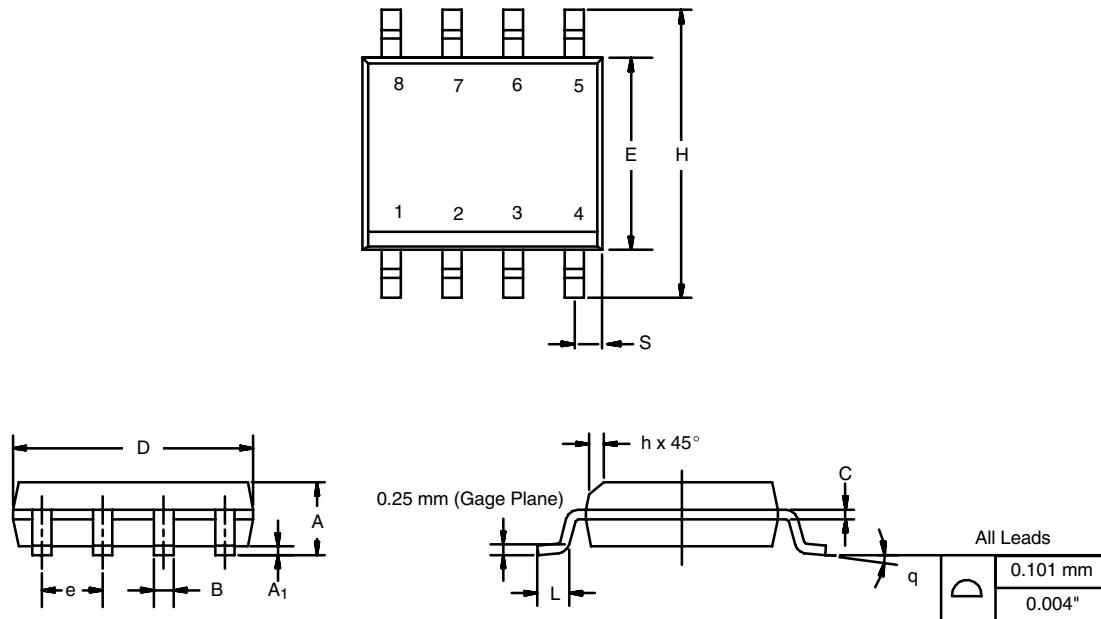
Power Derating, Junction-to-Ambient

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

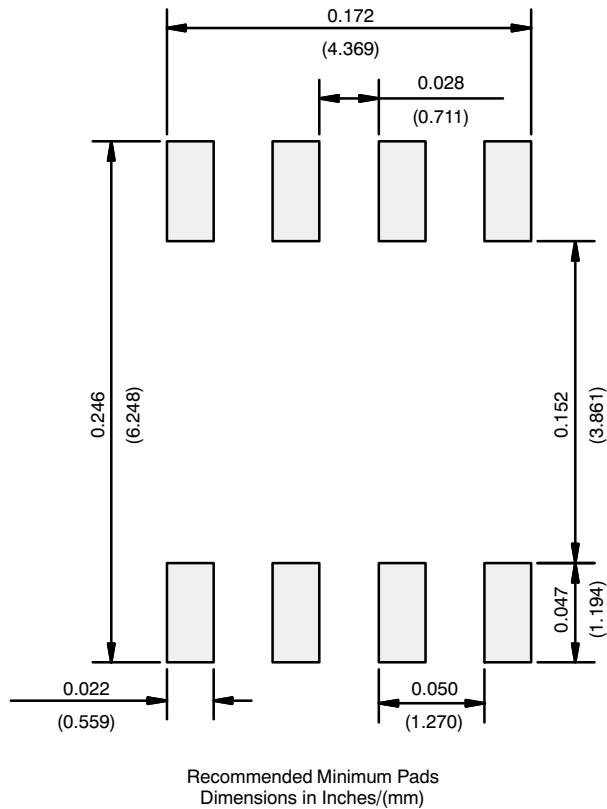
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

**RECOMMENDED MINIMUM PADS FOR SO-8**

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